

## IN THE CLAIMS

1 – 7 (canceled) (election)

8. (original) A method of operating a semiconductor device comprising:  
applying an operating voltage to said semiconductor device; and  
applying a fractional negative voltage to a second surface of said  
semiconductor device.

9. (original) The method of Claim 8 wherein said fractional negative voltage  
is applied by a wafer test machine.

10. (original) The method of Claim 8 wherein said fractional negative voltage  
is applied to said semiconductor device within a semiconductor package.

11. (original) The method of Claim 8 wherein said fractional negative voltage  
is produced by said semiconductor device.

12. (original) The method of Claim 8 wherein said fractional negative voltage  
is less than about 50 millivolts in magnitude.

13 – 28 (canceled) (election)

29. (original) A method comprising:  
supplying a positive voltage to a top surface of a semiconductor wafer;  
testing said semiconductor wafer;  
responsive to a failure of said testing, applying a fractional negative  
voltage to a bottom side of a substrate of said wafer; and  
retesting said semiconductor wafer with said negative voltage applied  
to said bottom side.

30. (original) The method of Claim 29 further comprising marking said wafer with a first pass indicator in response to passing said testing.

31. (original) The method of Claim 29 further comprising marking said wafer with a second pass indicator in response to passing said retesting.

32. (original) The method of Claim 30 and further comprising binning said wafer based on said first pass indicator.

33. (original) The method of Claim 29 further comprising testing said wafer at least a third time responsive to a failure of said retesting.

34. (original) The method of Claim 29 further comprising rejecting said wafer as defective responsive to a failure of said retesting.

35. (original) The method of Claim 29 further comprising repeating said testing, applying and retesting for a plurality of wafers.